

NCE P-Channel Enhancement Mode Power MOSFET

Description

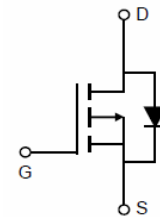
The NCE60P03Y uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for use as a load switch or in PWM applications.

General Features

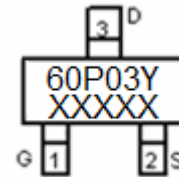
- $V_{DS} = -60V, I_D = -3A$
 $R_{DS(ON)} < 84m\Omega @ V_{GS} = -10V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

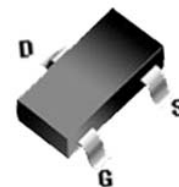
- Load switch
- PWM application



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60P03Y	NCE60P03Y	SOT-23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-3	A
Pulsed Drain Current ^(Note 1)	I_{DM}	-16	A
Maximum Power Dissipation	P_D	1.5	W
Single pulse avalanche energy ^(Note 5)	E_{AS}	72	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	83.3	$^\circ C/W$
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Electrical Characteristics ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						

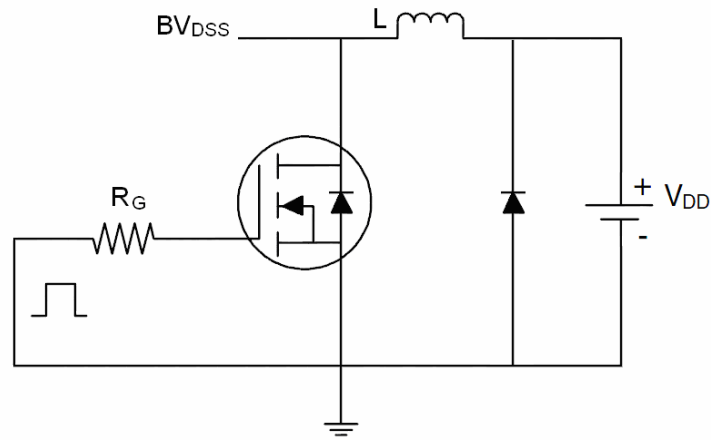
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-3A	-	62	84	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-3A	-	8	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	799	-	PF
Output Capacitance	C _{OSS}		-	50	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	42	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =10Ω, V _{GS} =-10V, R _G =3Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-3A, V _{GS} =-10V	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	3.4	-	nC
Gate-Drain Charge	Q _{gd}		-	4.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-3A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-3	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 3A di/dt = -100A/μs (Note3)	-	24		nS
Reverse Recovery Charge	Q _{rr}		-	29		nC

Notes:

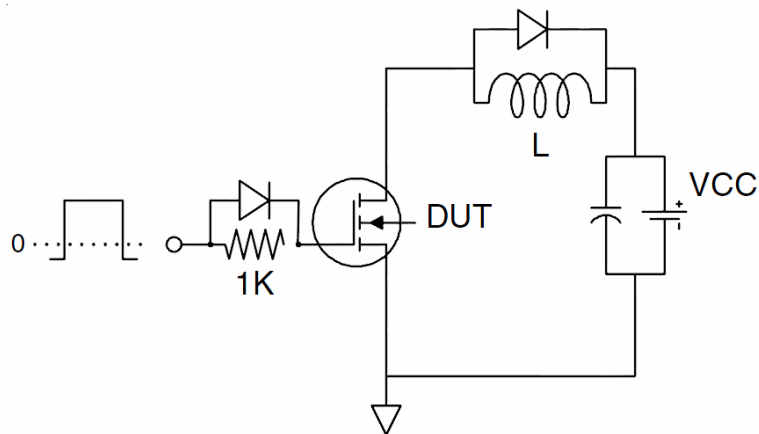
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ C, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

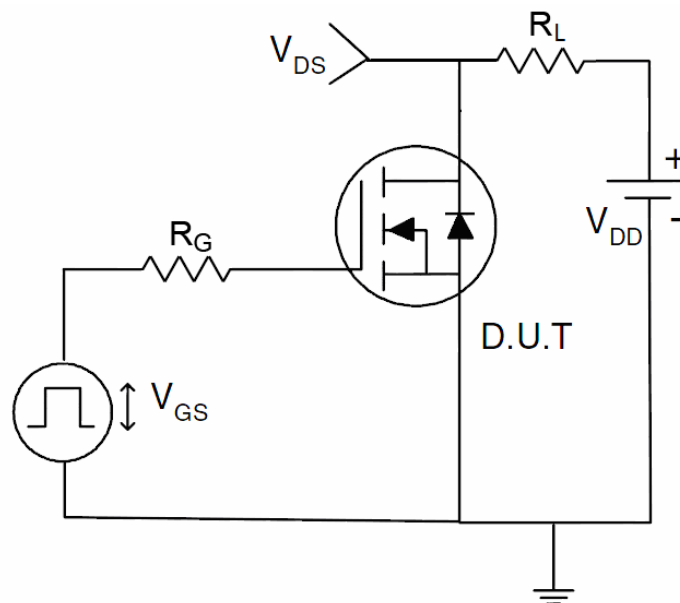
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

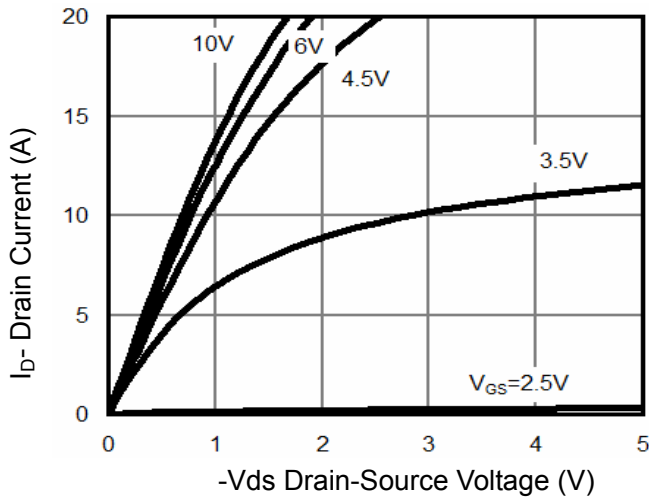


Figure 1 Output Characteristics

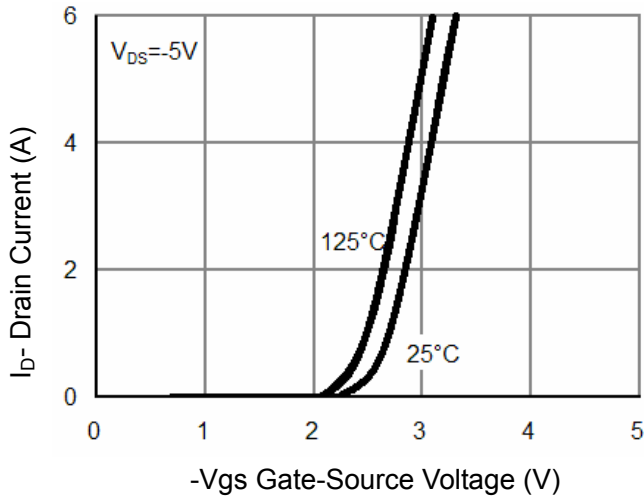


Figure 2 Transfer Characteristics

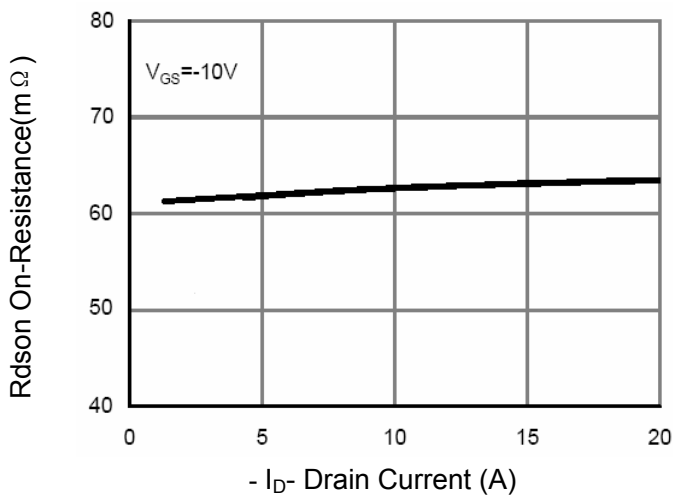


Figure 3 Rdson- Drain Current

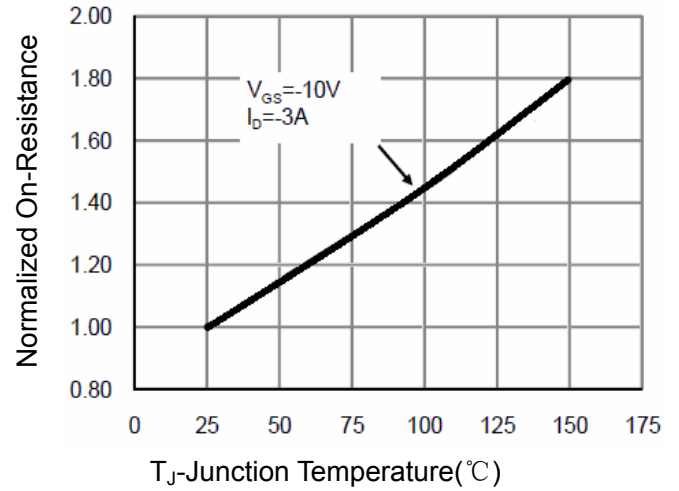


Figure 4 Rdson-Junction Temperature

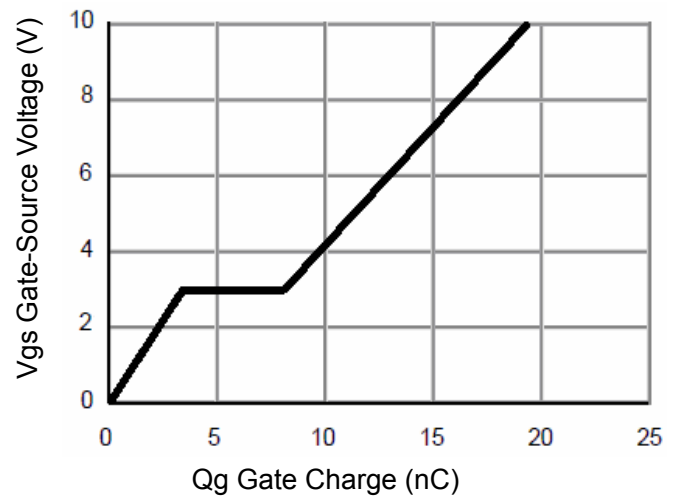


Figure 5 Gate Charge

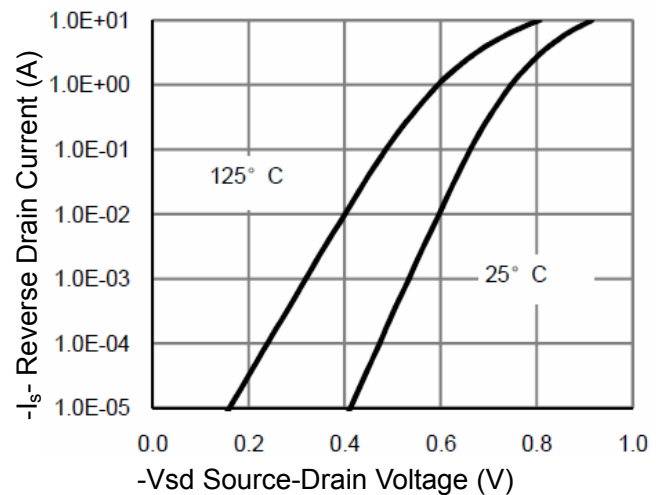


Figure 6 Source- Drain Diode Forward

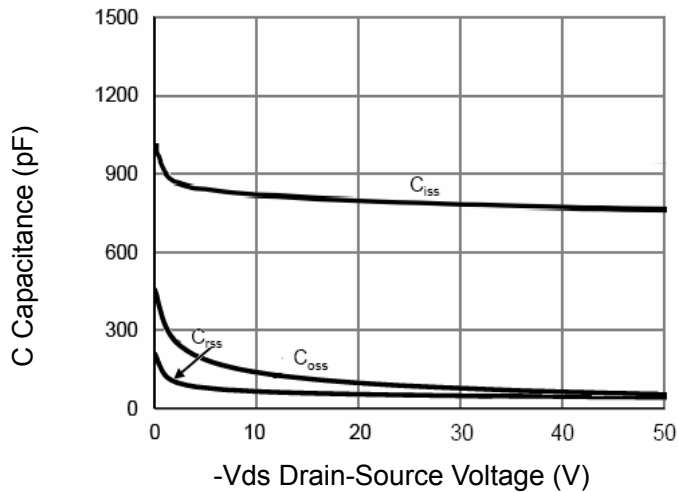


Figure 7 Capacitance vs Vds

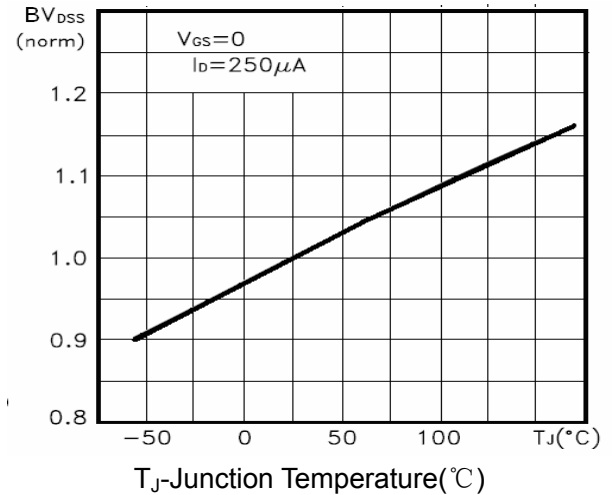


Figure 9 BV_{DSS} vs Junction Temperature

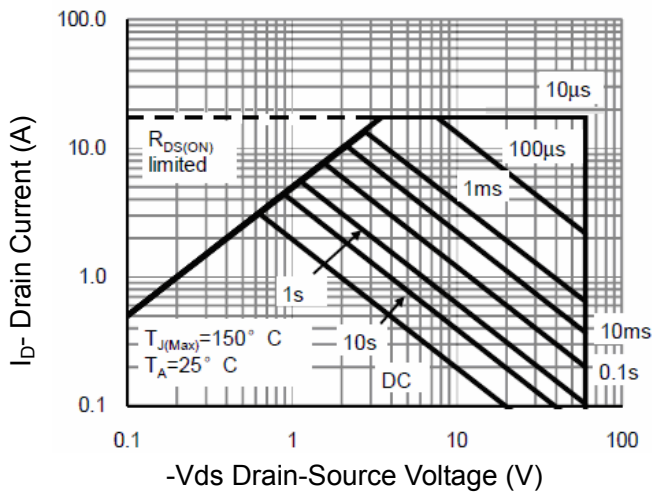


Figure 8 Safe Operation Area

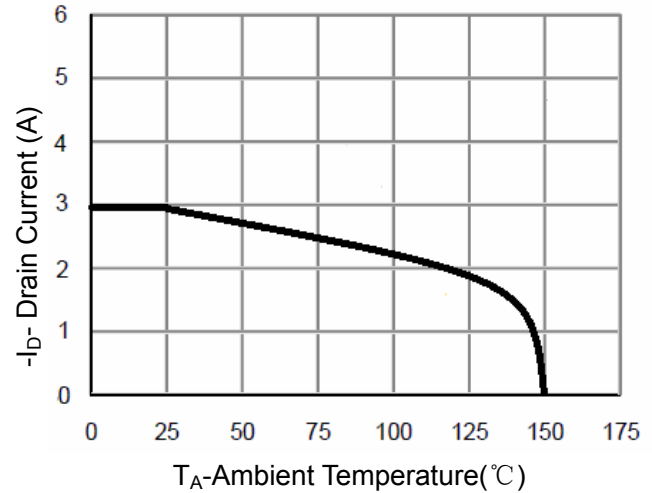


Figure 10 I_D Current De-rating

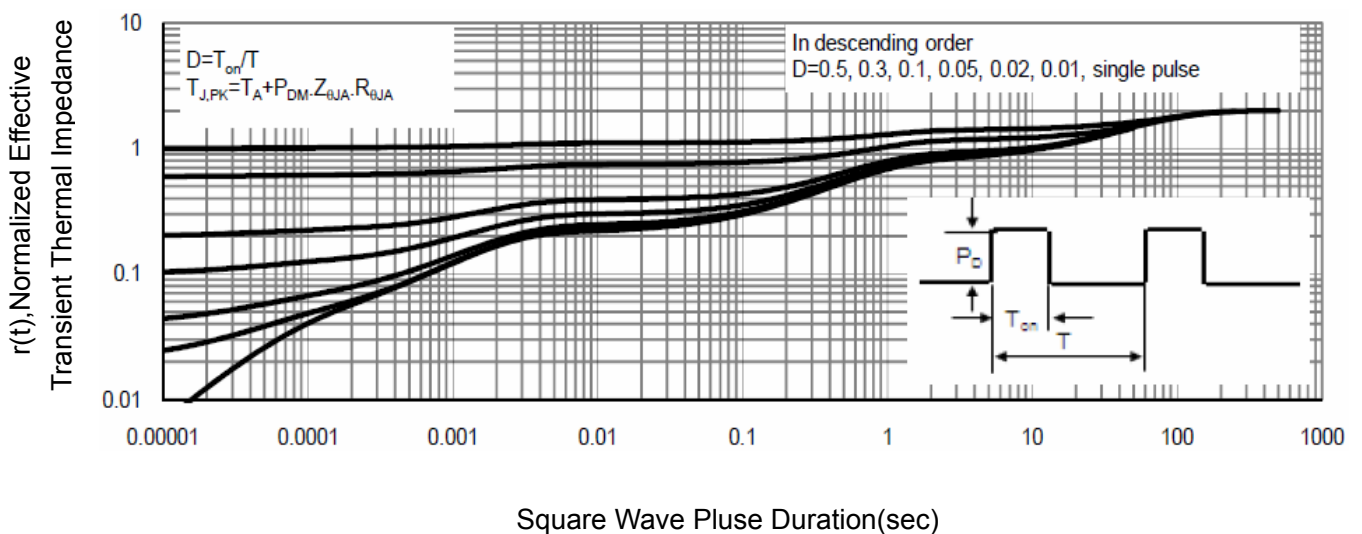
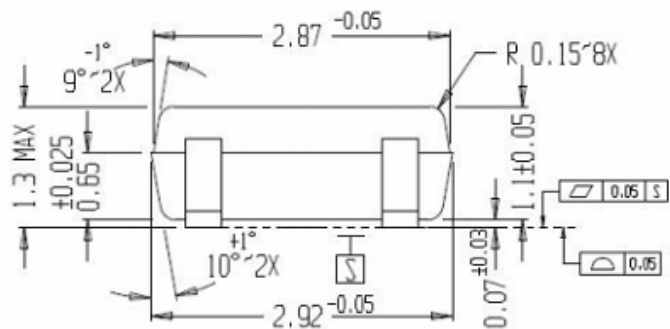
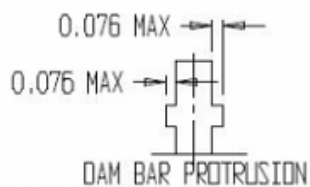
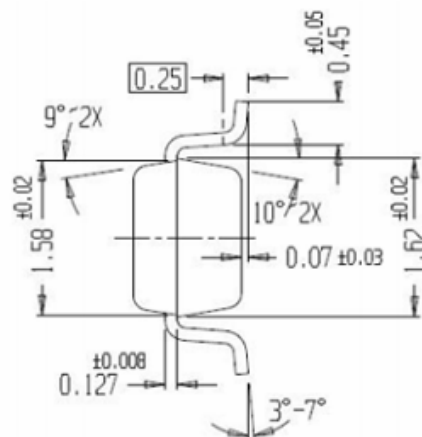
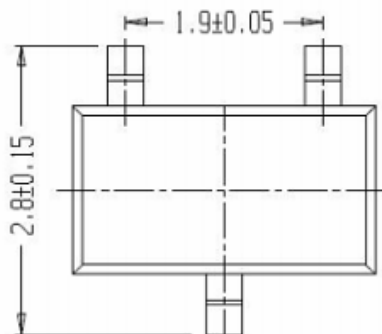


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-23-3L Package Information



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